



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-251/TO-252-2L Plastic-Encapsulate Transistors

3CA753 TRANSISTOR (PNP)

FEATURES

Power dissipation

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-2	A
P_C	Collector power dissipation	1.2	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

TO-251
TO-252-2L



1.BASE
2.COLLECTOR
3.EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-2\text{V}, I_C=-500\text{mA}$	100		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2\text{A}, I_B=-200\text{mA}$			-0.8	V
	$V_{CE(sat)}$	$I_C=-1.5\text{A}, I_B=-30\text{mA}$			-2	V
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-500\text{mA}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		13		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y	G
Range	100-200	160-320	200-400
Marking			

Typical Characteristics

3CA753

